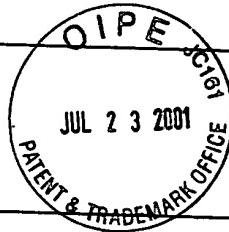


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ATTY. DOCKET NO. UF-222XC2D2	SERIAL NO. 09/735,217
APPLICANT(S): Tim Anderson	
FILING DATE 12/12/2000	GROUP 2813

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER							DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
LAC	AA	5	6	2	5	2	0	2	4/1997	Chai			
	AB												10/23/00
	AC												JUL 26 2001
	AD												RE-SEARCHED
	AE												MAIL ROOM
	AF												

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
LAC	AG	0	8	4	6	7	9	1	10/1998	EPO			
	AH												
	AI												
	AJ												

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

LAC	AK	1	S. Nakamura, M. Senoh, S. Nagahama, N. Iwasa, et al., "Continuous-wave operation of InGaN/GaN/AlGaN-based laser diodes grown on GaN substrates" 1998 <i>Appl. Phys. Lett.</i> , 72, 16, 2014.									
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LAC	AM	3	H. Morkoc, S. Strite, G.B. Gao, M.E. Lin, B. Sverdlov and M. Burns, "Large-band-gap SiC, III-V nitride, and II-VI ZnSe based semiconductor device technologies" 1994 <i>J. Appl. Phys.</i> 76, 1367.									
LAC	AN	4	T.P. Chow and Tyagi, "Wide Bandgap Compound Semiconductors for Superior High-Voltage Unipolar Power Devices" 1994 IEEE Trans. Electron Devices, 41, 1481.									
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LAC	AS	9	Shuji Nakamura, "InGaN/GaN/AlGaN-Based Laser Diodes with an Estimated Lifetime of Longer Than 10,000 Hours" 1998 MRS Bulletin.									
EXAMINER	<i>LAC</i>							DATE CONSIDERED <i>7/11/03</i>				

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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